

AN 1987:449765 HCAPLUS
 DN 107:49765
 TI Optical recording films
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 SO Jpn. Kokai Tokkyo Koho, 9 pp.
 CODEN: JKXXAF
 DT Patent
 LA Japanese
 FAN.CNT 1

	PATENT NO.	KIND	DATE	APPLICATION NO.	DATE
PI	JP 62047839	A2	19870302	JP 1985-185877	19850826
PRAI	JP 1985-185877		19850826		

AB An optical recording film has a composition of $A_xB_yS_zT_m$ ($0 \leq x \leq 30$, $10 \leq y \leq 70$, $30 \leq z \leq 80$, $0 \leq m < 30$ atomic%, and B = Sn and/or Pb). A may be ≥ 1 of Zn, Cd, Hg, Al, Ga, In, Tl, C, Bi, B, N, P, O, S, F, lanthanide elements, actinide elements, and inert gas elements (e.g., < 30 atomic%); Si, Ge, As, and Sb (e.g., < 10 atomic%); and Ti, Ni, Co, Sc, Y, Zr, V, Nb, Cr, Mo, Mn, Fe, Ru, Rh, Pd, Ta, and Pt (e.g., < 1 atomic%). The composition may have $0.3 < y/(y+z) \leq 0.4$ with $10 \leq m \leq 25$. A Si_3N_4 layer 40-nm thick, a $Sn_{28}Se_{57}Te_{15}$ layer 100-nm thick, and a Si_3N_4 layer 40-nm thick were formed on a glass substrate. A disk was formed by bonding 2 substrates prepared on the sides of Si_3N_4 protective films using a UV-cured resin. A signal output > 100 mV was obtained.